L Number	Hits	Search Text	DB	Time stamp
1	2	("6674667").PN.	USPAT; US-PGPUB;	2004/07/26 07:46
4	13763	metal adj oxide adj semiconductor adj field adj effect adj transistor	-EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:47
5	3	apply\$6 adj2 third adj voltage near1 potential adj3 gate	DERWENT USPAT; US-PGPUB;	2004/07/26 07:47
9	6	(apply\$6 adj2 first adj voltage near1 potential adj3 source) or (apply\$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide	EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:47
10	5	((apply\$6 adj2 first adj voltage near1 potential adj3 source) or (apply\$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide) and conduction adj1 channel	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/26 07:47
11	2	(((apply\$6 adj2 first adj voltage near1 potential adj3 source) or (apply\$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide) and conduction adj1 channel) and	USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:47
12	2	negative adj gate adj1 potential near3 conduction adj1 channel (((apply\$6 adj2 first adj voltage near1 potential adj3 source) or (apply\$6 adj2 second adj voltage near1 potential adj3 drain) and gate adj1 oxide) and conduction adj1 channel) and	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:47
13	0	negative adj gate adj1 potential apply\$6 adj2 negative adj3 voltage near1 potential adj3 gate near5 MOSFEt	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:47
16	862	apply\$6 adj2 negative adj3 voltage adj3 gate	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:47
17	5020	apply\$6 adj2 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:47
18	5020	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:47
19	1107	(apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate) and MOSFET	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:47
20	269	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate near5 mosfet	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:47
21	108	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate near5 mosfet	DERWENT US-PGPUB; EPO; JPO;	2004/07/26 07:47
2	3	"20020110033" or (("6674667").PN.)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:48
3	2	"20020110033"	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:48
6	3	apply\$6 adj2 third adj3 voltage near1 potential adj3 gate	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:48

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	7	6	apply\$6 adj2 first adj voltage near1 potential adj3 source	USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:48
				DERWENT	
	8	7	apply\$6 adj2 second adj voltage near1 potential adj3 drain	USPAT;	2004/07/26 07:48
1	•	•	applyto adja occora adj vortago rioar i potentiar adje arami	US-PGPUB;	
				EPO; JPO;	
				DERWENT	
	14	6	apply\$6 adj2 negative adj3 voltage near1 potential adj3 gate	USPAT;	2004/07/26 07:48
				US-PGPUB;	
				EPO; JPO;	
				DERWENT	
	15	18	(("4,051,354") or ("5,324,681") or ("5,327,380") or	USPAT;	2004/07/26 07:48
			("5,493,141") or ("5,764,096") or ("5,768,192") or ("5,781,477")	US-PGPUB;	
			or ("6,038,168") or ("6,229,733")).PN.	EPO; JPO;	
	00	464	anni-96 adid nagativa adi (CAS AD Hatanay AD Lagatral AD L	DERWENT USPAT	2004/07/26 07:49
ļ	22	161	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ circuit) bias adj3 voltage adj3 gate near5 mosfet	USPAT	2004/07/26 07:48
	23	153	apply\$6 adj1 negative adj (CAS ADJ latency ADJ control ADJ	USPAT	2004/07/26 07:48
- 1	23	133	circuit) bias adj1 voltage adj3 gate near5 mosfet	OSFAI	2004/01/20 01.40
	24	153	apply adj1 negative adj (CAS ADJ latency ADJ control ADJ	USPAT	2004/07/26 07:48
			circuit) bias adj1 voltage adj3 gate near5 mosfet		
İ	25	153	appl\$ adj1 negative adj (CAS ADJ latency ADJ control ADJ	USPAT	2004/07/26 07:48
- 1			circuit) bias adj1 voltage adj3 gate near5 mosfet		
	26	31	(appl\$ adj1 negative adj (CAS ADJ latency ADJ control ADJ	USPAT	2004/07/26 07:48
İ			circuit) bias adj1 voltage adj3 gate near5 mosfet) and negative		
			adj1 voltage		
	27	7	ONO adj anti adj1 fuse	USPAT;	2004/07/26 07:48
				US-PGPUB;	
				EPO; JPO;	
	20	2	"20020225077"	DERWENT	2004/07/26 07:49
	28	2	"20030235077"	USPAT; US-PGPUB;	2004/07/26 07:48
				EPO; JPO;	
				DERWENT	
	29	2	"20030235085"	USPAT;	2004/07/26 07:48
		_		US-PGPUB;	
				EPO; JPO;	÷ · ·
				DERWENT	
	30	2	("5324681").PN.	USPAT;	2004/07/26 07:48
1				US-PGPUB;	
				EPO; JPO;	
	0.4		(157040001) DN	DERWENT	2004/07/00 07:40
	31	2	("5764096").PN.	USPAT; US-PGPUB;	2004/07/26 07:48
				EPO; JPO;	
	•			DERWENT	
	32	29	metal adj oxide adj semiconductor adj field adj effect adj	USPAT;	2004/07/26 07:48
			transistor near3 switch\$6 adj element	US-PGPUB;	
			,	EPO; JPO;	
				DERWENT	
	33	37		USPAT;	2004/07/26 07:52
			("5,172,204") or ("5,414,658") or ("5,544,118") or ("5,763,912")	US-PGPUB;	
			or ("5,828,099") or ("5,851,893") or ("5,867,425") or	EPO; JPO;	
Ì			("5,978,273") or ("6,180,957") or ("6,243,298") or ("6,272,042")	DERWENT	
			or ("6,452,835") or ("6,456,535") or ("6,504,762") or		
	34	19	("6,510,086") or ("6,664,601")).PN. (("3,992,701") or ("4,761,768") or ("4,766,569") or	USPAT	2004/07/26 07:54
i	J 4	19	((3,992,701)) or (4,761,768) or (4,766,569) or (5,763,912")	USPAI	2004/07/20 07:54
			or ("5,828,099") or ("5,851,893") or ("5,867,425") or		
		ĺ	("5,978,273") or ("6,180,957") or ("6,243,298") or ("6,272,042")		
1		,	or ("6,452,835") or ("6,456,535") or ("6,504,762") or		
			("6,510,086") or ("6,664,601")).PN.		
Į	35	1	("6700821").PN.	USPAT	2004/07/26 07:54

37	2	("6521958").PN.	USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:55	
38	2	("20040114433").PN.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/07/26 07:55	_
36	3	("6700821").PN.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 07:57	